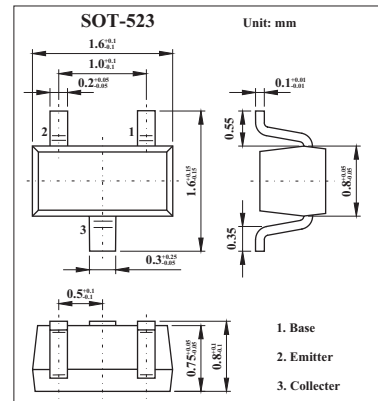


**BAS16T;BAW56T
BAV70T;BAV99T**

■ Features



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Limits	Unit
Power dissipation ($T_{a\text{ mb}}=25^\circ\text{C}$)	P_D	150	mW
Forward Current	I_F	75	mA
Reverse Voltage	V_R	85	V
Operating and storage junction temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100 \mu\text{A}$	85		V
Reverse voltage leakage current	I_R	$V_R = 75\text{ V}$		2	μA
		$V_R = 25\text{ V}$		0.03	
Forward voltage	V_F	$I_F = 1\text{ mA}$		715	mV
		$I_F = 10\text{ mA}$		855	
		$I_F = 50\text{ mA}$		1000	
		$I_F = 150\text{ mA}$		1250	
Diode capacitance	C_D	$V_R=0\text{ V}, f=1\text{MHz}$		1.5	pF
Reverse recovery time	t_{rr}			4	ns

■ Marking

Type	BAS16T	BAW56T	BAV70T	BAV99T
Marking	A2	JD	JJ	JE